

Refine Search

Search Results -

Terms	Documents
L1 and (implant same (RTN or thermal nitridation))	11

Database:

- US Pre-Grant Publication Full-Text Database
- US Patents Full-Text Database
- US OCR Full-Text Database
- EPO Abstracts Database
- JPO Abstracts Database
- Derwent World Patents Index
- IBM Technical Disclosure Bulletins

Search:

L10

Refine Search

Recall Text

Clear

Interrupt

Search History

DATE: Thursday, March 17, 2005 [Printable Copy](#) [Create Case](#)

Set Name	Query	Hit Count	Set Name
side by side			result set
DB=PGPB,USPT,USOC,EPAB,JPAB,DWPI,TDBD; PLUR=YES; OP=ADJ			
<u>L10</u>	L1 and (implant same (RTN or thermal nitridation))	11	<u>L10</u>
<u>L9</u>	L8 and RTN	3	<u>L9</u>
<u>L8</u>	L1 and "ghyka"	426	<u>L8</u>
<u>L7</u>	L6 and "ghyka"	0	<u>L7</u>
<u>L6</u>	L5 and RTN	20	<u>L6</u>
<u>L5</u>	(438/791-794).ccls.	676	<u>L5</u>
<u>L4</u>	L1 and ((RTN or thermal nitridation) same silicon same trench)	27	<u>L4</u>
<u>L3</u>	L1 and ((RTN or thermal nitridation) same silicon)	442	<u>L3</u>
<u>L2</u>	L1 and (RTN or thermal nitridation)	758	<u>L2</u>
<u>L1</u>	(438/\$).ccls.	167846	<u>L1</u>

END OF SEARCH HISTORY